

AMENDMENTS TO THE CLAIMS

Please cancel claims 25-27 and 38, add new claim 39, and amend the claims as follows:

1-21. (Cancelled)

22. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:

an atomic layer deposition (ALD) chamber having a reaction chamber;

a housing having an inlet for receiving a carrier gas and an outlet in fluid communication with a sealable interior volume, wherein the outlet is operably coupled to the reaction chamber of the atomic layer deposition (ALD) chamber;

at least two surfaces comprising a mesh material contained in the housing having a solid tantalum-containing chemical precursor applied thereto, ~~wherein the solid chemical precursor includes a tantalum-containing precursor or a tungsten-containing precursor;~~ and

a heating member contained within a wall of the housing, wherein at least one of the at least two surfaces is in thermal communication with the wall of the housing.

23. (Previously Presented) The apparatus of claim 22, wherein the at least two surfaces are spaced to allow passage of the carrier gas therebetween.

24. (Previously Presented) The apparatus of claim 22, wherein the at least two surfaces are formed of a material selected from the group consisting of stainless steel and ceramic.

25-28. (Cancelled)

29. (Previously Presented) The apparatus of claim 22, wherein a heating member is contained in one of the at least two surfaces.

30. (Previously Presented) The apparatus of claim 22, wherein one of the at least two surfaces is coupled to the housing.

31. (Previously Presented) The apparatus of claim 22, wherein the at least two surfaces have a form selected from the group consisting of an s-shape, a linear shape, and a cone shape.

32. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:

an atomic layer deposition (ALD) chamber having a reaction chamber;

a housing having an inlet for receiving a carrier gas and an outlet in fluid communication with a sealable interior volume, wherein the outlet is operably coupled to the reaction chamber of the atomic layer deposition (ALD) chamber;

at least two cone shaped surfaces contained in the housing having a solid tantalum-containing chemical precursor applied thereto; and

a heating member contained within a wall of the housing, wherein at least one of the at least two surfaces is in contact ~~thermal communication~~ with the wall of the housing.

33. (Previously Presented) The apparatus of claim 32, wherein the at least two surfaces are spaced to allow passage of the carrier gas therebetween.

34. (Previously Presented) The apparatus of claim 32, wherein the at least two surfaces are formed of a material selected from the group consisting of stainless steel and ceramic.

35. (Cancelled)

36. (Previously Presented) The apparatus of claim 32, wherein a heating member is contained in one of the at least two surfaces.

37. (Previously Presented) The apparatus of claim 32, wherein one of the at least two surfaces is coupled to the housing.

38. (Cancelled)

39. (New) The apparatus of claim 22, wherein the at least one of the at least two surfaces is in contact with the wall of the housing.